

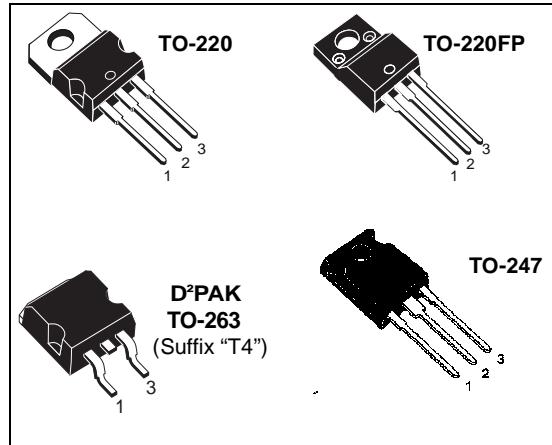


STB80NF12 STW80NF12 STP80NF12 STP80NF12FP

N-CHANNEL 120V-0.013Ω-80A TO-220/TO-247/TO-220FP/D²PAK
STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{D(on)}	I _D
STB80NF12	120 V	<0.018 Ω	80 A(*)
STP80NF12	120 V	<0.018 Ω	80 A(*)
STP80NF12FP	120 V	<0.018 Ω	80 A(*)
STW80NF12	120 V	<0.018 Ω	80 A(*)

- TYPICAL R_{D(on)} = 0.013Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION
- SURFACE-MOUNTING D²PAK (TO-263) POWER PACKAGE IN TUBE (NO SUFFIX) OR IN TAPE & REEL (SUFFIX "T4")



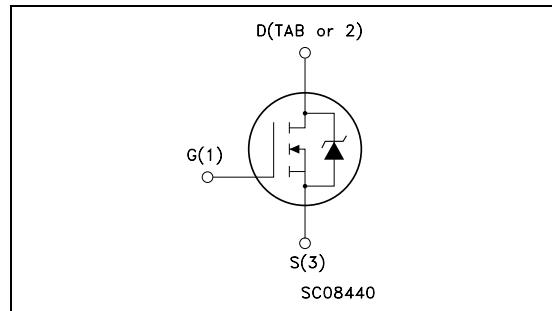
DESCRIPTION

This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

APPLICATIONS

- HIGH-EFFICIENCY DC-DC CONVERTERS
- UPS AND MOTOR CONTROL

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STB_P_W80NF12	STP80NF12FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	120	120	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	120	120	V
V _{GS}	Gate-source Voltage	± 20	± 20	V
I _{D(*)}	Drain Current (continuous) at T _C = 25°C	80	80(#)	A
I _D	Drain Current (continuous) at T _C = 100°C	60	60(#)	A
I _{DM(•)}	Drain Current (pulsed)	320	320(#)	A
P _{tot}	Total Dissipation at T _C = 25°C	300	45	W
	Derating Factor	2.0	0.3	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	10	10	V/ns
E _{AS} (2)	Single Pulse Avalanche Energy	700	700	mJ
V _{ISO}	Insulation Withstand Voltage (DC)	-----	2500	V
T _{stg}	Storage Temperature	-55 to 175		°C
T _j	Operating Junction Temperature			

(*) Pulse width limited by safe operating area.

(*) Limited by Package

(2) I_{SD} ≤ 35A, di/dt ≤ 300A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

(#) Refer to SOA for the max allowable current values on FP-type due to thermal resistance value.

(1) Starting T_j = 25 °C, I_D = 40A, V_{DD} = 45V

STB80NF12 STW80NF12 STP80NF12 STP80NF12FP

THERMAL DATA

			TO-247	D ² PAK TO-220	TO-220FP	
R _{thj-case}	Thermal Resistance Junction-case	Max	0.5	0.5	3.33	°C/W
R _{thj-amb} T_I	Thermal Resistance Junction-ambient Maximum Lead Temperature For Soldering Purpose	Max 300	50 300	62.5 300	62.5 300	°C/W °C

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^\circ\text{C}$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0$	120			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating } T_C = 125^\circ\text{C}$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			± 100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu\text{A}$	2			V
$R_{DS(\text{on})}$	Static Drain-source On Resistance	$V_{GS} = 10 \text{ V}$ $I_D = 40 \text{ A}$		0.013	0.018	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} = 15 \text{ V}$ $I_D = 40 \text{ A}$		80		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{V}$ $f = 1 \text{ MHz}$ $V_{GS} = 0$		4300 600 230		pF pF pF

STB80NF12 STW80NF12 STP80NF12 STP80NF12FP

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 50 \text{ V}$ $I_D = 40 \text{ A}$ $R_G = 4.7 \Omega$ $V_{GS} = 10 \text{ V}$ (Resistive Load, Figure 3)		40 145		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 80 \text{ V}$ $I_D = 80 \text{ A}$ $V_{GS} = 10 \text{ V}$		140 23 51	189	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 50 \text{ V}$ $I_D = 40 \text{ A}$ $R_G = 4.7 \Omega$, $V_{GS} = 10 \text{ V}$ (Resistive Load, Figure 3)		134 115		ns ns

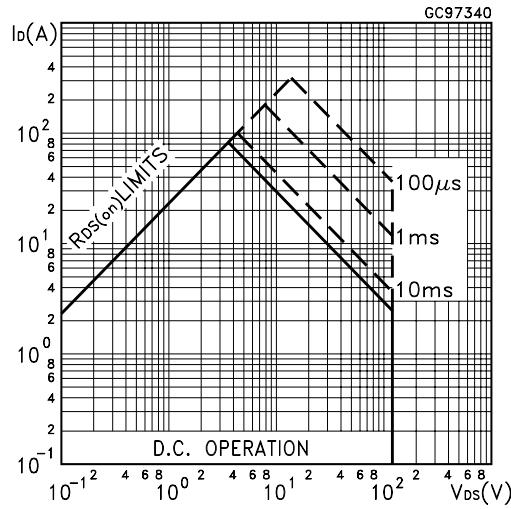
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (*)$	Source-drain Current Source-drain Current (pulsed)				80 320	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 80 \text{ A}$ $V_{GS} = 0$			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 80 \text{ A}$ $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 35 \text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		155 0.85 11		ns nC A

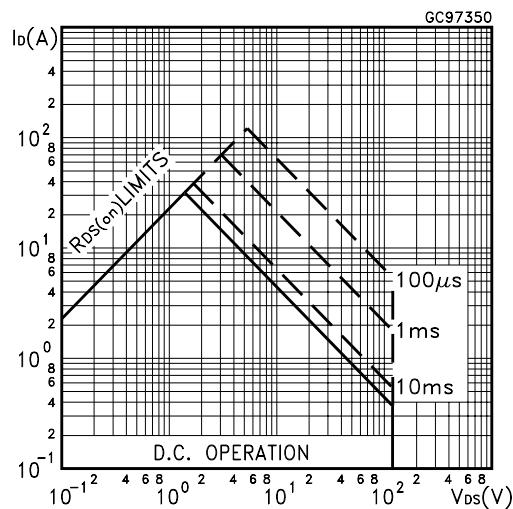
(*)Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

(•)Pulse width limited by safe operating area.

Safe Operating Area

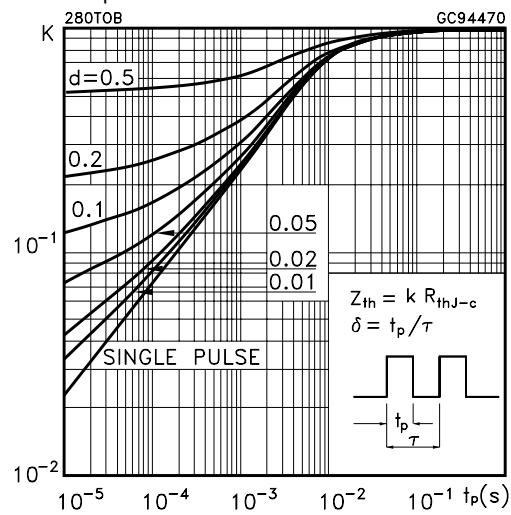


Safe Operating Area for TO-220FP

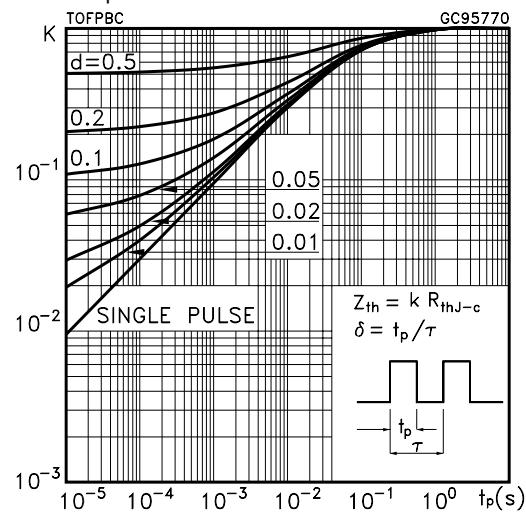


STB80NF12 STW80NF12 STP80NF12 STP80NF12FP

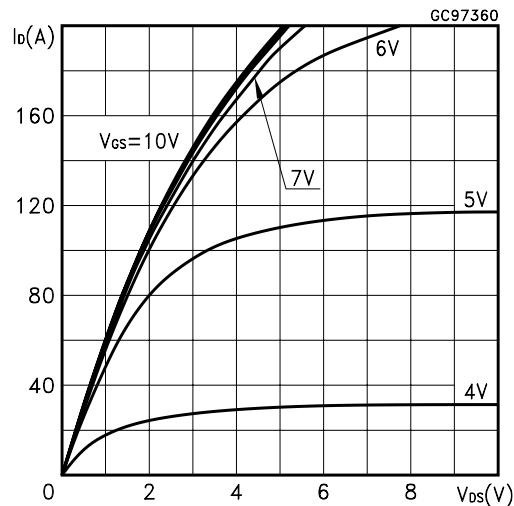
Thermal Impedance



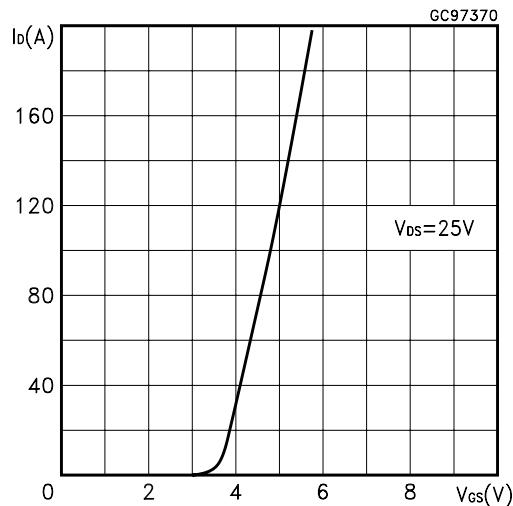
Thermal Impedance for TO-220FP



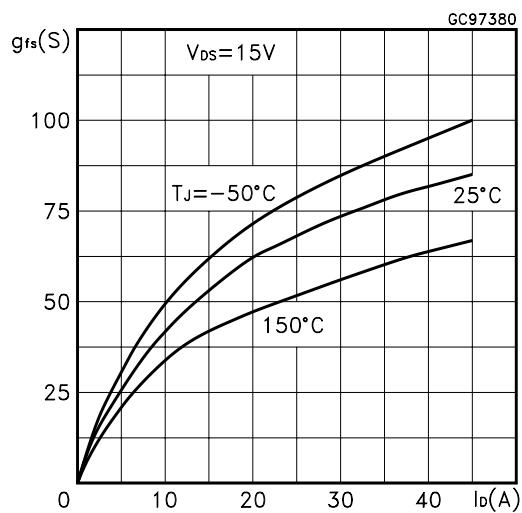
Output Characteristics



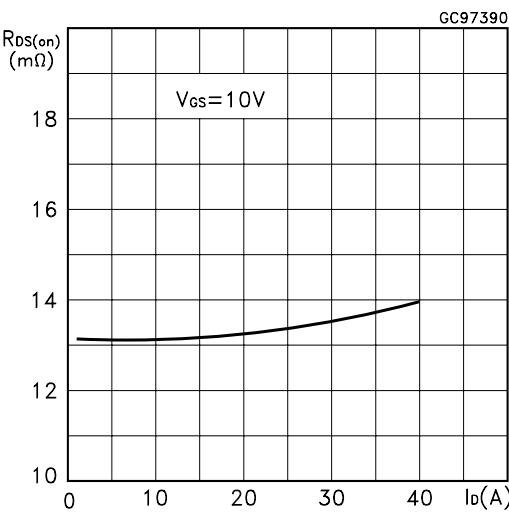
Transfer Characteristics



Transconductance

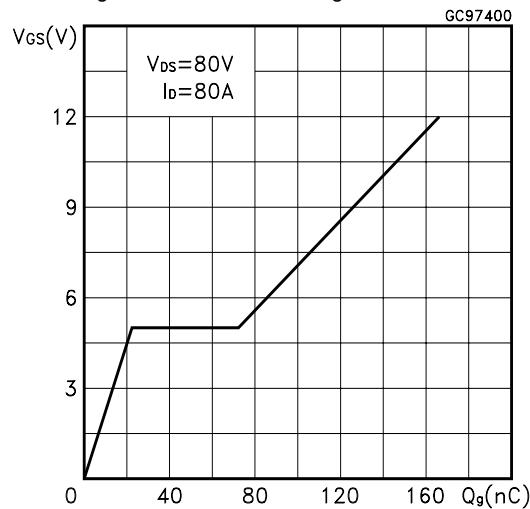


Static Drain-source On Resistance

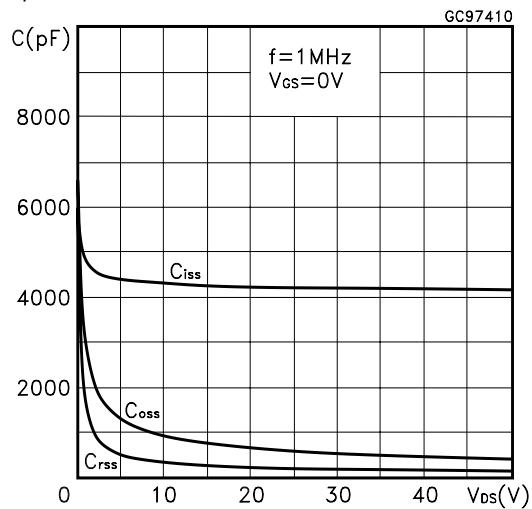


STB80NF12 STW80NF12 STP80NF12 STP80NF12FP

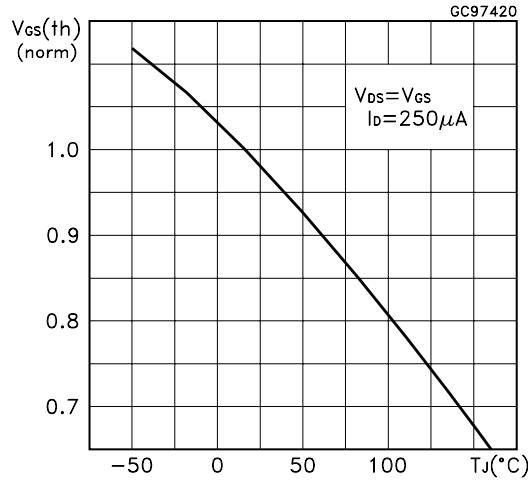
Gate Charge vs Gate-source Voltage



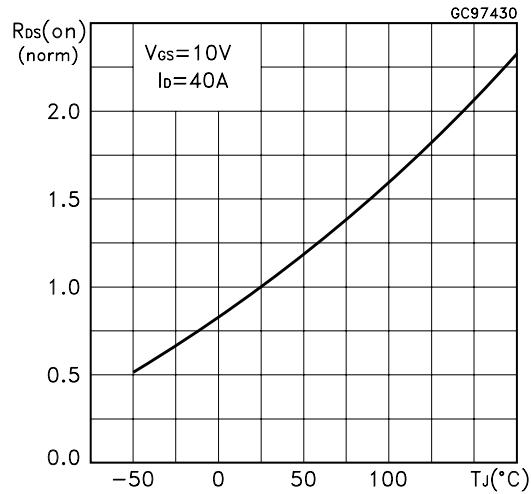
Capacitance Variations



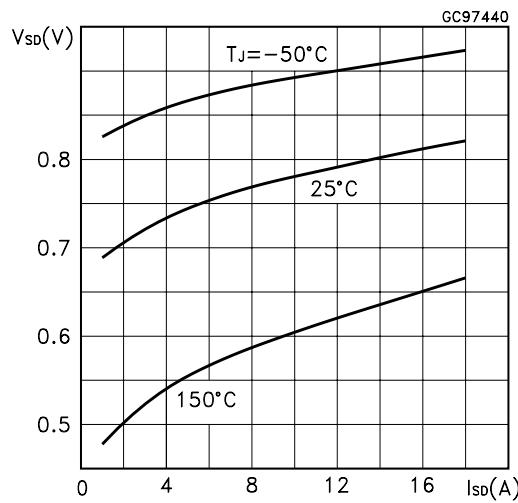
Normalized Gate Threshold Voltage vs Temperature



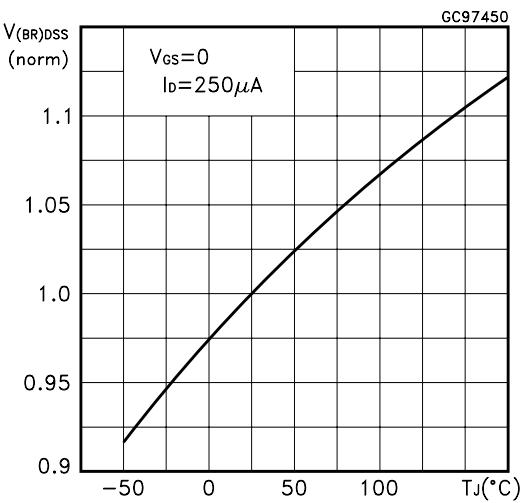
Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage Temperature



STB80NF12 STW80NF12 STP80NF12 STP80NF12FP

Fig. 1: Unclamped Inductive Load Test Circuit

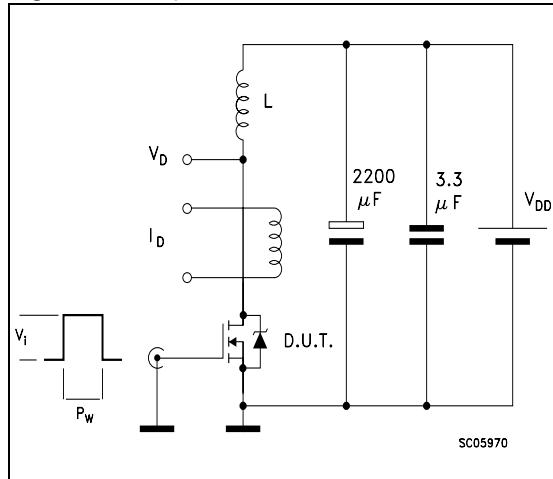


Fig. 2: Unclamped Inductive Waveform

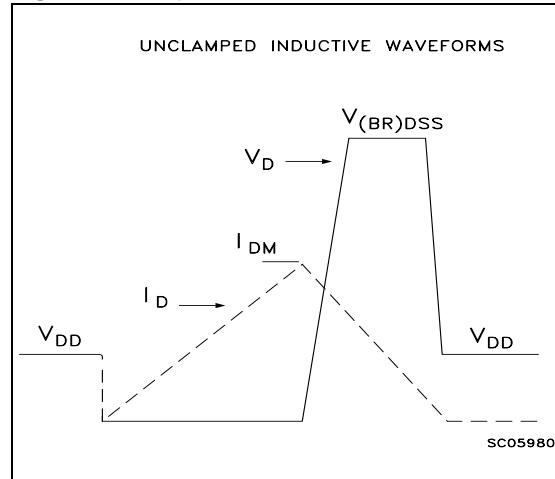


Fig. 3: Switching Times Test Circuits For Resistive Load

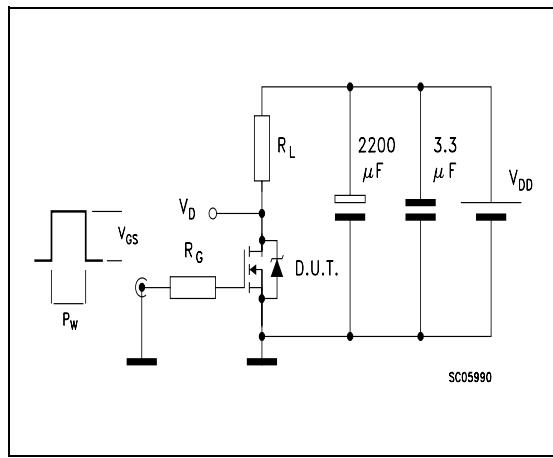


Fig. 4: Gate Charge test Circuit

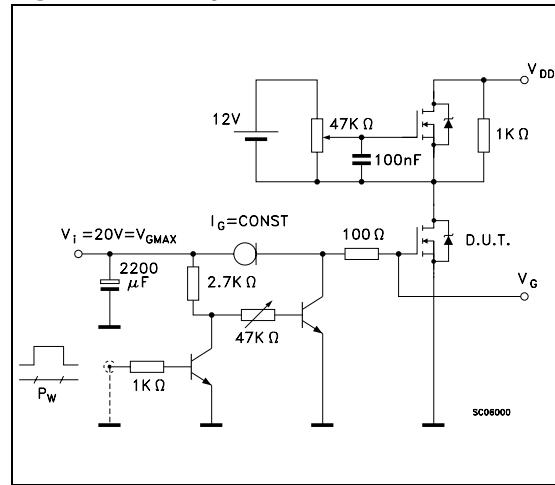
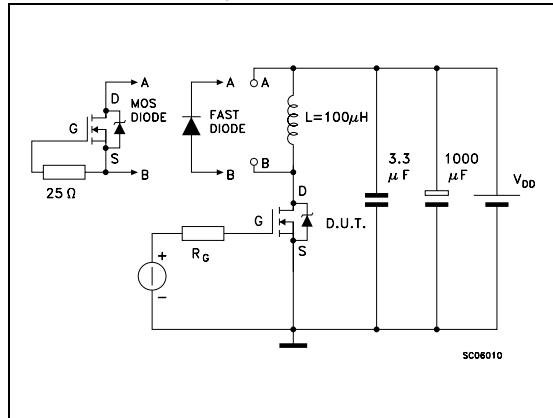


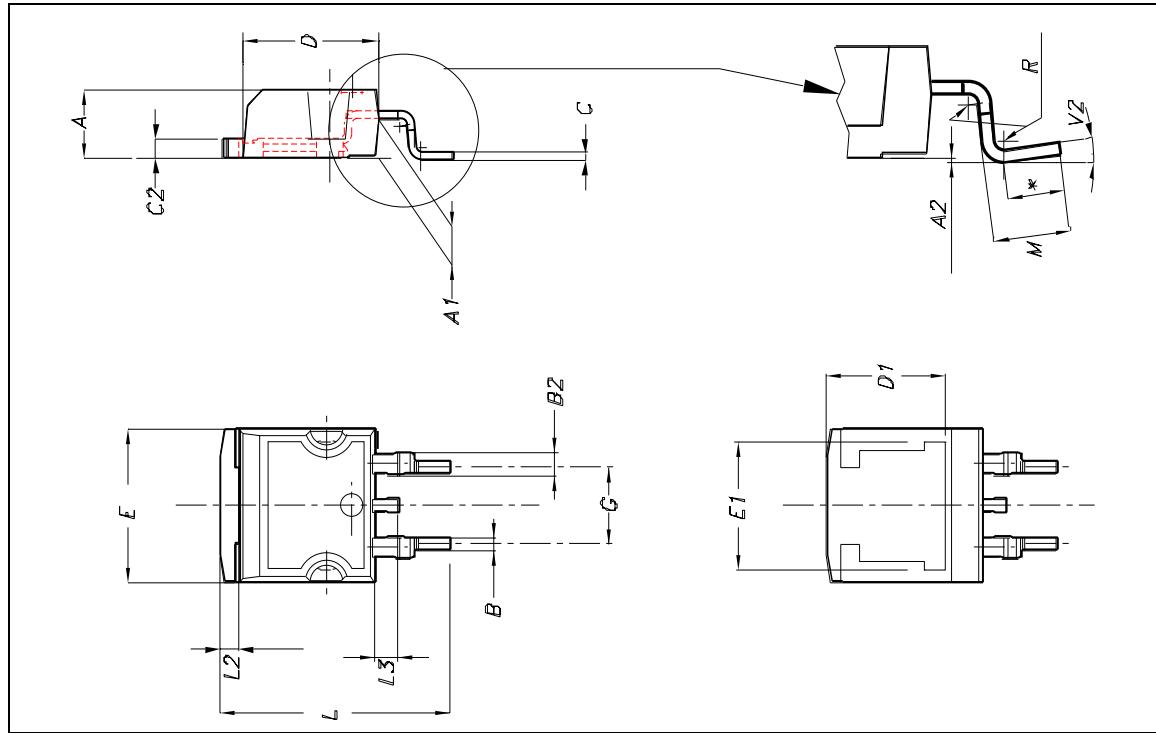
Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



STB80NF12 STW80NF12 STP80NF12 STP80NF12FP

D²PAK MECHANICAL DATA

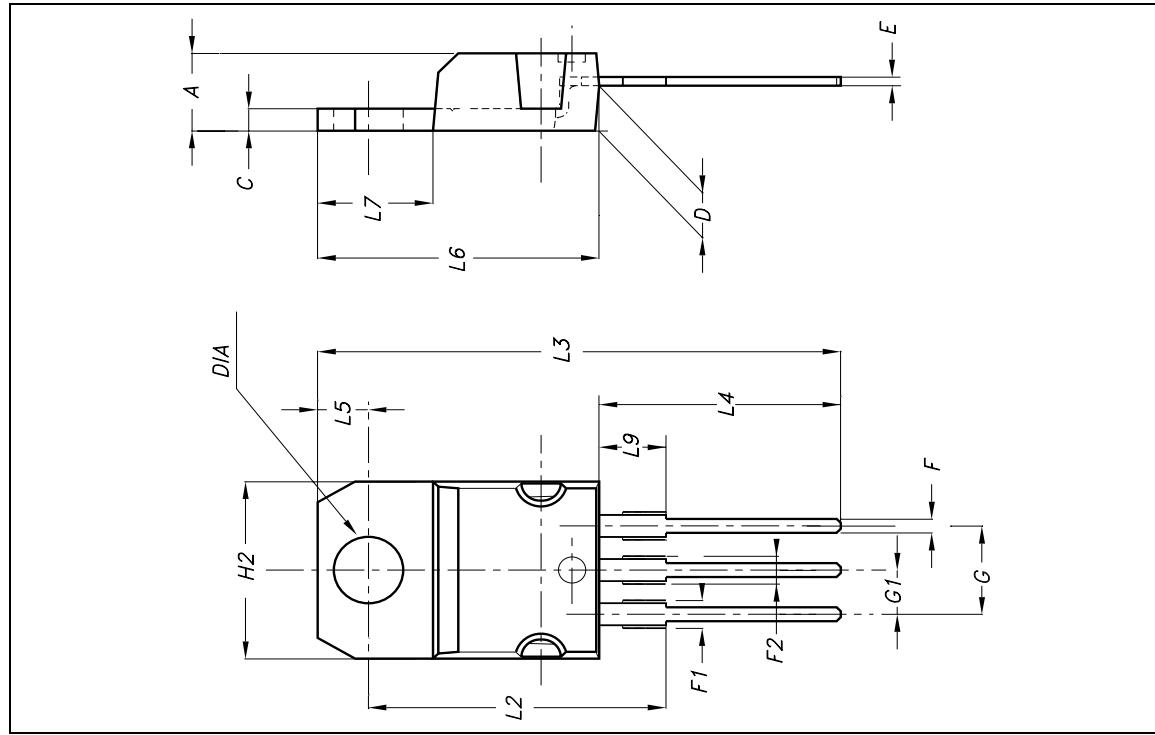
DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1	8.5				0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.016	
V2	0°		8°	0°		8°



STB80NF12 STW80NF12 STP80NF12 STP80NF12FP

TO-220 MECHANICAL DATA

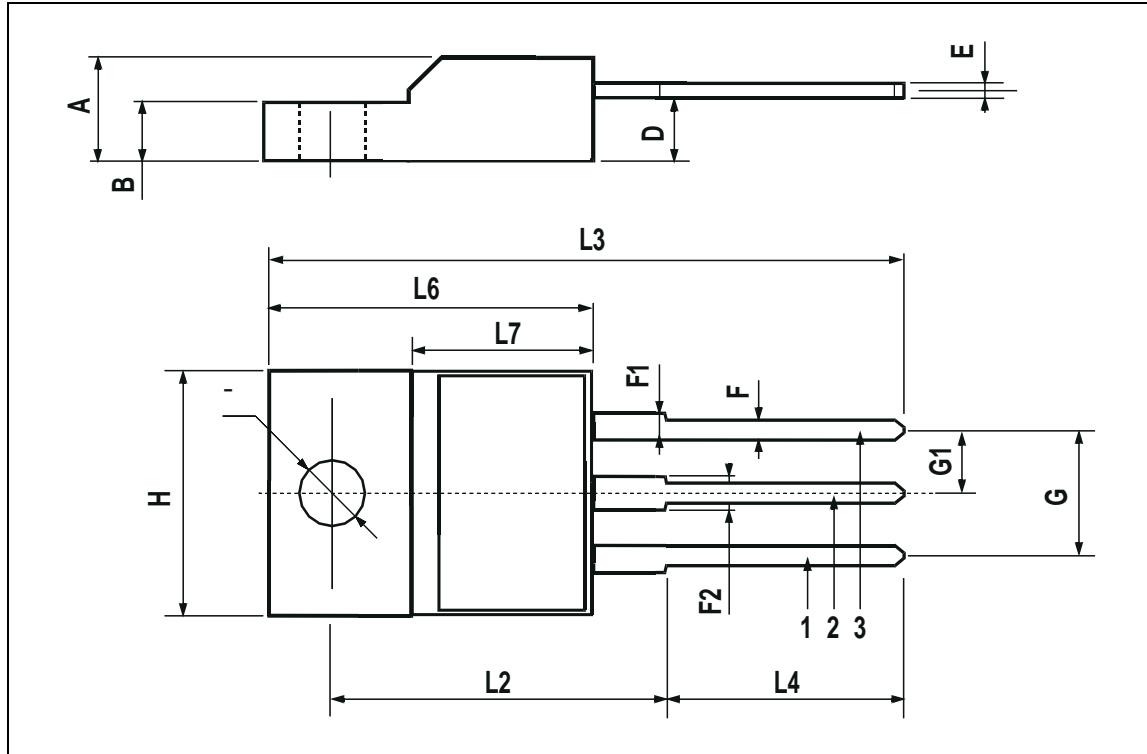
DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.40		2.70	0.094		0.106
H2	10		10.40	0.393		0.409
L2		16.40			0.645	
L3		28.90			1.137	
L4	13		14	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
DIA	3.75		3.85	0.147		0.151



STB80NF12 STW80NF12 STP80NF12 STP80NF12FP

TO-220FP MECHANICAL DATA

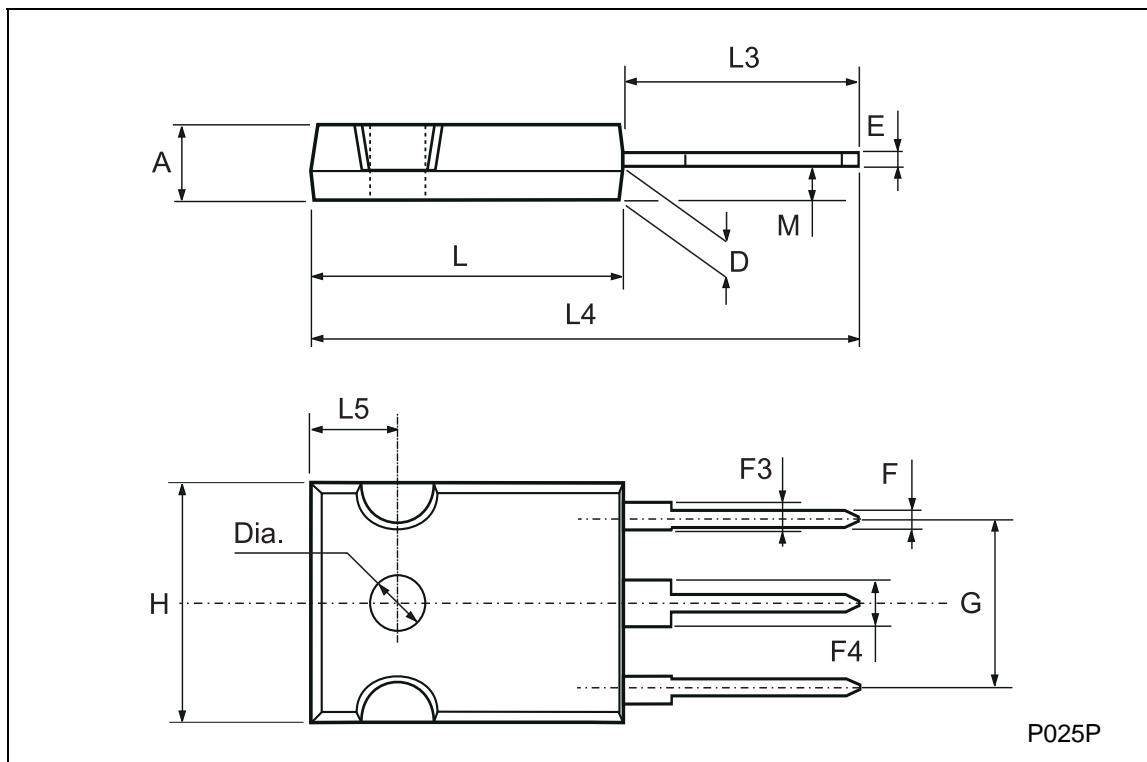
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
\emptyset	3		3.2	0.118		0.126



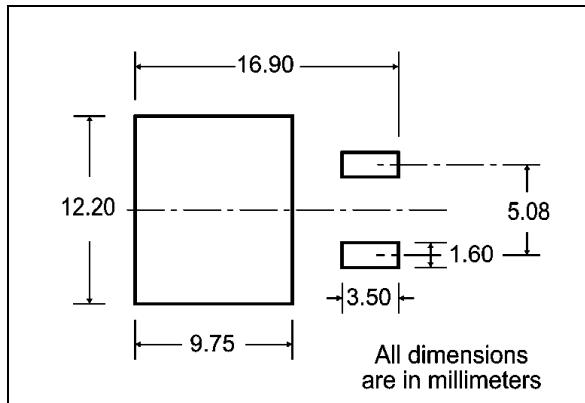
STB80NF12 STW80NF12 STP80NF12 STP80NF12FP

TO-247 MECHANICAL DATA

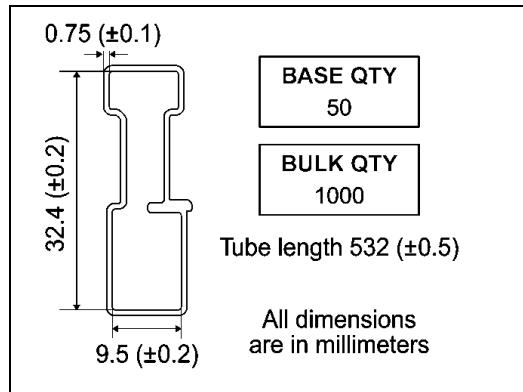
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559		0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118



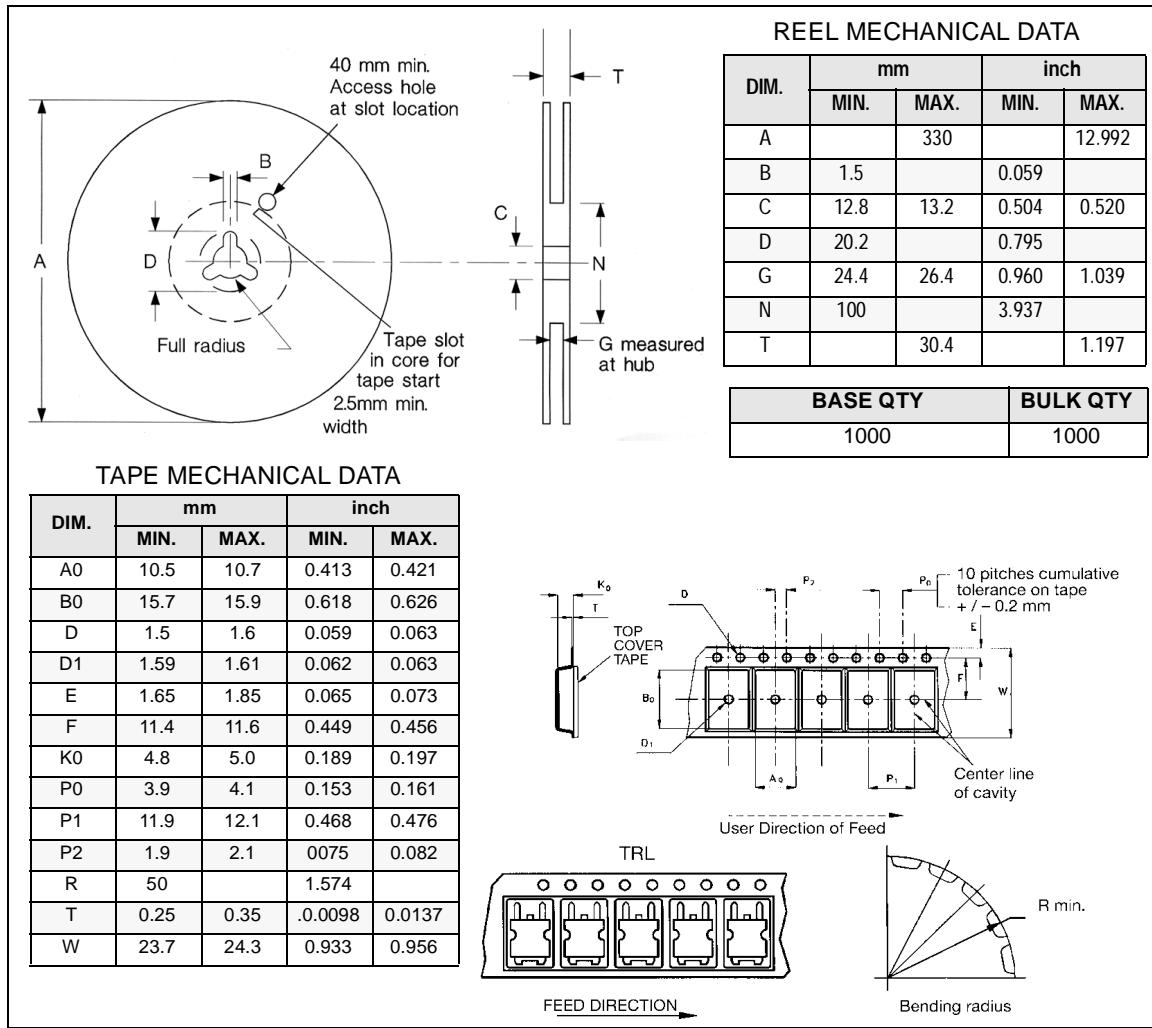
D²PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



* on sales type



STB80NF12 STW80NF12 STP80NF12 STP80NF12FP

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is registered trademark of STMicroelectronics
© 2003 STMicroelectronics - All Rights Reserved

All other names are the property of their respective owners.

STMicroelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco -
Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>